

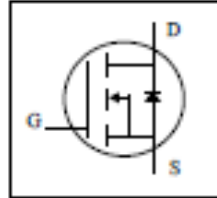
JTMA14SL50H-HF

Halogen-Free Product

N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- ▼ 100% R_g & UIS Test
- ▼ Fast Switching Characteristic
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free



V _{DS} @ T _J max	550V
R _{DS(ON)}	0.28Ω
I _D	13A



Description

JTMA14SL50 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power JTMAplications.

The TO-252 package is widely preferred for commercial-Industrial surface mount JTMAplications and suited for low voltage JTMAplications] such as DC/DC converters.

Absolute Maximum Ratings@T_J=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	500	V
V _{GS}	Gate-Source Voltage	+20	V
I _D @T _C =25°C	Drain Current, V _{GS} @ 10V ³	13	A
I _D @T _C =100°C	Drain Current, V _{GS} @ 10V ³	8.2	A
I _{DM}	Pulsed Drain Current ¹	32	A
dv/dt	MOSFET dv/dt Ruggedness (V _{GS} = 0 ...400V)	50	V/ns
P _D @T _C =25°C	Total Power Dissipation	89.2	W
P _D @T _A =25°C	Total Power Dissipation ⁴	2	W
E _{AS}	Single Pulse Avalanche Energy ⁵	108	mJ
dv/dt	Peak Diode Recovery dv/dt ⁶	15	V/ns
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Units
R _{θj-c}	Maximum Thermal Resistance, Junction-case	1.4	°C/W
R _{θj-a}	Maximum Thermal Resistance, Junction-ambient (PCB mount) ⁴	62.5	°C/W

Data & specifications subject to change without notice

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有需要详细的文件请发邮件: oumao18@jtm-ic.com 联系或电话: 0755-262580208